


ARTICLE



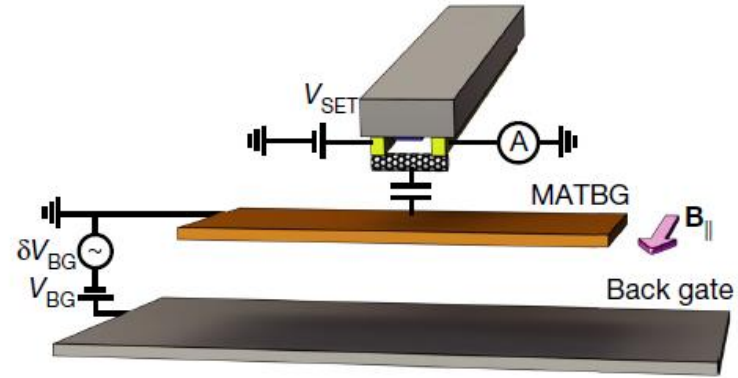
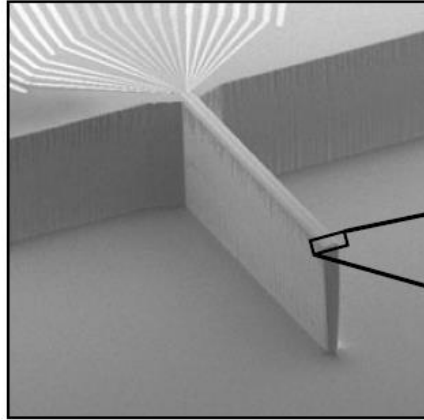
<https://doi.org/10.1038/s41467-020-16001-5>

OPEN

# Atomic-like charge qubit in a carbon nanotube enabling electric and magnetic field nano-sensing

I. Khivrich<sup>1</sup> & S. Ilani <sup>1</sup>✉

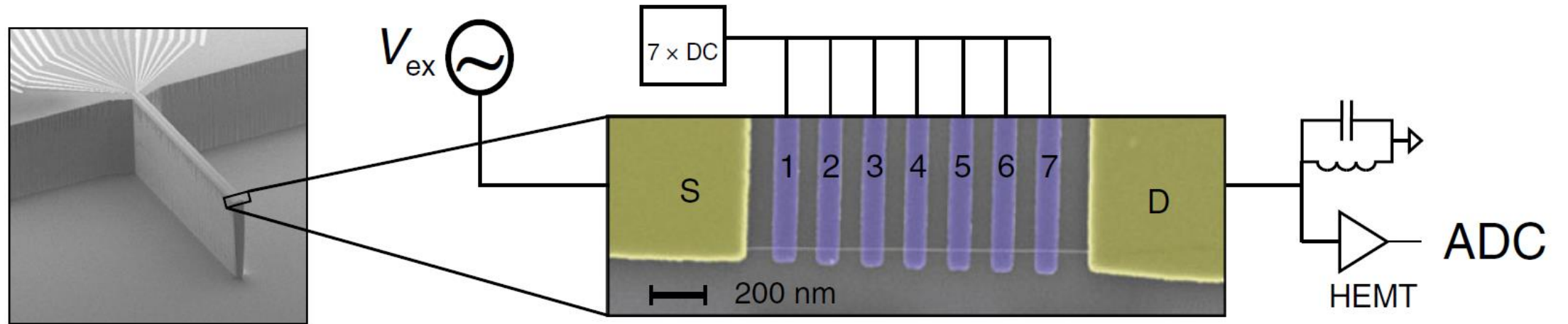
# Scanning probe of electric and magnetic fields



Advantages qubits defined in carbon nanotubes (CNTs) for scanning probe microscopy:

- Very high sensitivity to electric fields (voltages, currents, charges, electronic density of states, ...)
- Sensitive to magnetic fields
- Relatively high resolution (QD size)
- Low invasiveness

# Device: carbon nanotube suspended over gates

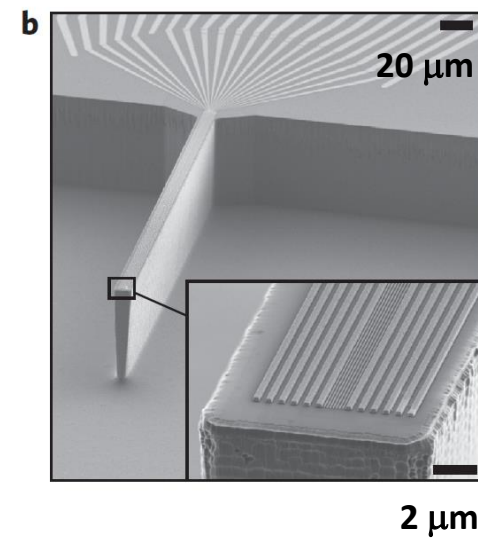
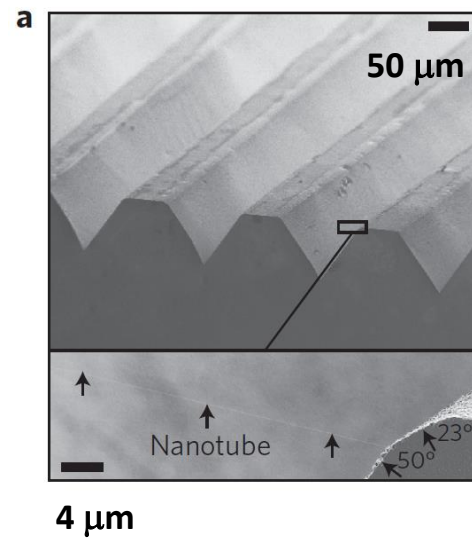
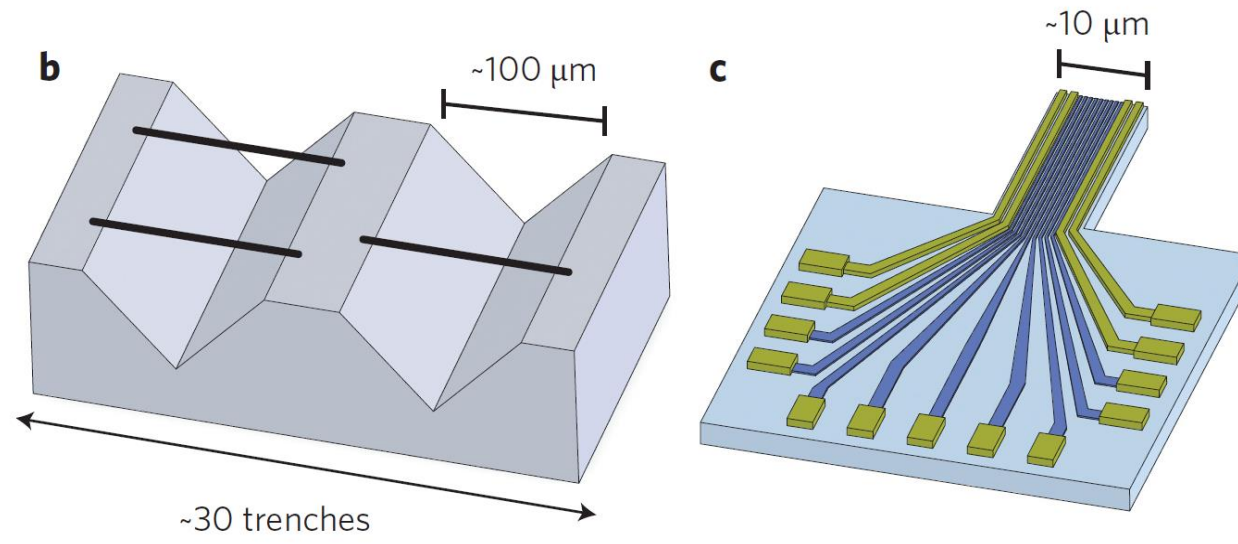


- To be used as scanning probe
- Here: on-chip characterization

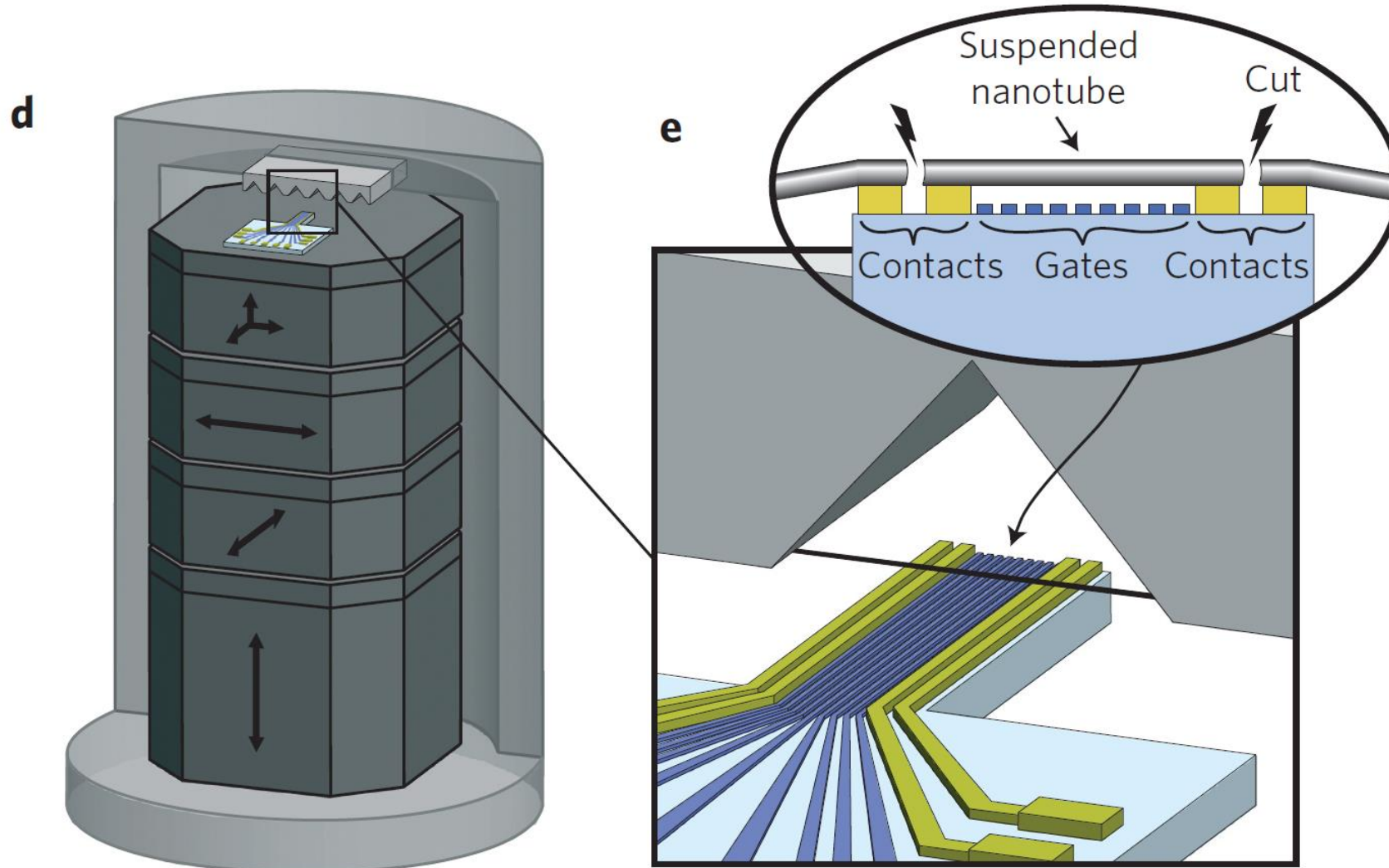
# Realization of pristine and locally tunable one-dimensional electron systems in carbon nanotubes

J. Weissman<sup>1,2†</sup>, M. Honig<sup>1†</sup>, S. Pecker<sup>1†</sup>, A. Benyamini<sup>1†</sup>, A. Hamo<sup>1†</sup> and S. Ilani<sup>1\*</sup>

# Fabrication

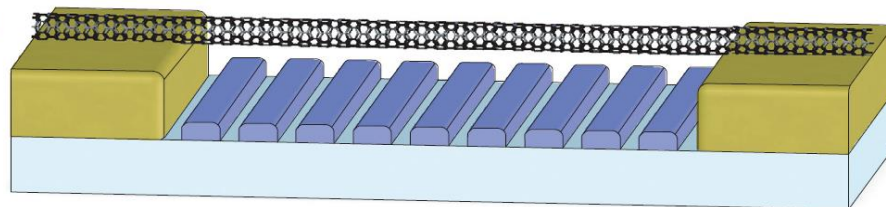
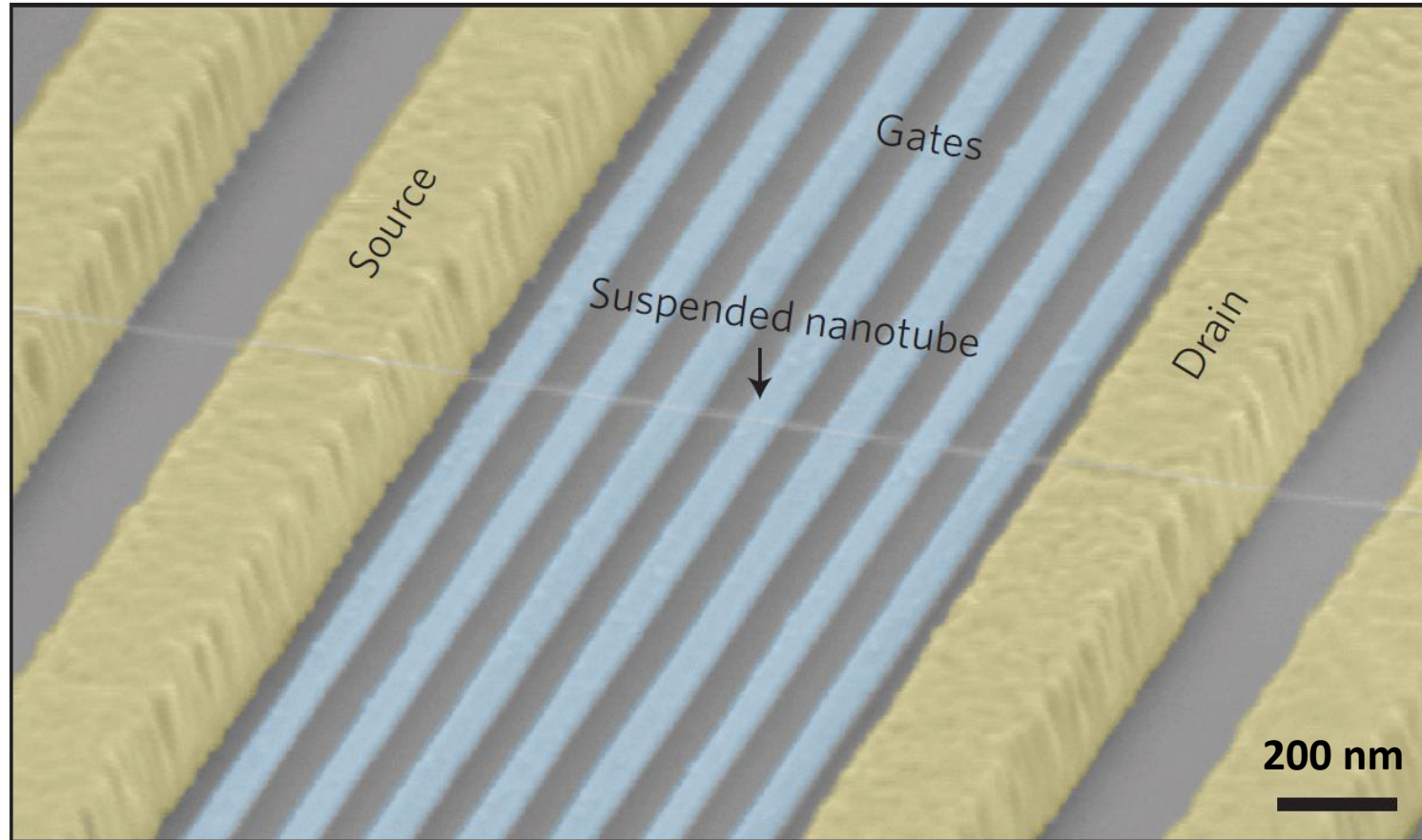


# Fabrication



- All inside a fridge @ 4K
- Argon ion etching in load-lock to improve contacting CNT

# Fabrication



## Here:

- CNT length =  $1.2\mu\text{m}$
- Suspension height: 60 nm
- 7 gates

## *Other recent research using these devices (Ilani group)*

*Nanomechanical pump–probe measurements of insulating electronic states in a carbon nanotube*  
Khivrich et al., *Nat. Nanotechnol.* 14, 161 (2019)

*Simultaneous voltage and current density imaging of flowing electrons in two dimensions*  
Ella et al., *Nat. Nanotechnol.* 14, 480 (2019)

*Imaging the electronic Wigner crystal in one dimension*  
Shapir et al., *Science* 364, 870, 2019)

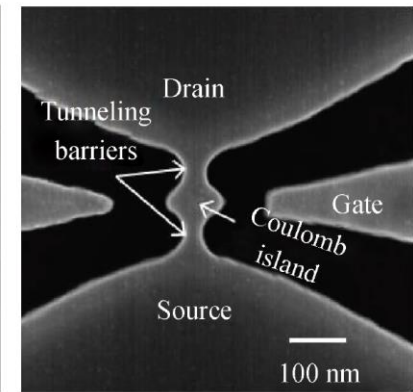
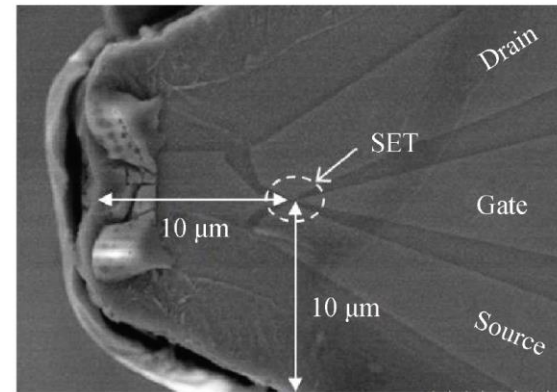
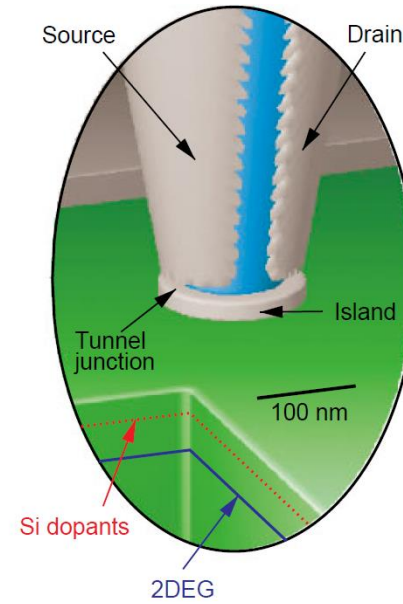
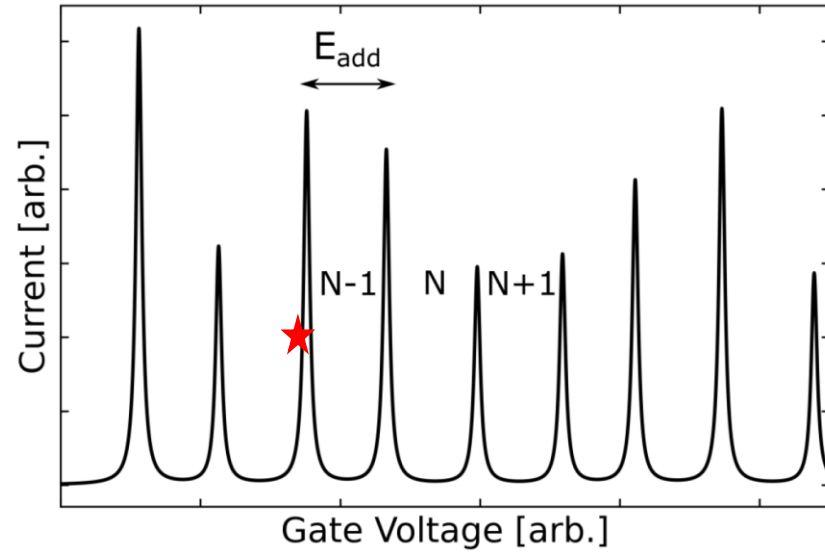
*Visualizing Poiseuille flow of hydrodynamic electrons*  
Sulpizio et al., *Nature* 576, 75 (2019)

*Cascade of Phase Transitions and Dirac Revivals in Magic Angle Graphene*  
Zondiner et al., *Nature* 582, 203 (2020)

*Entropic evidence for a Pomeranchuk effect in magic-angle graphene*  
Rozen et al., *Nature* 592, 214 (2021)



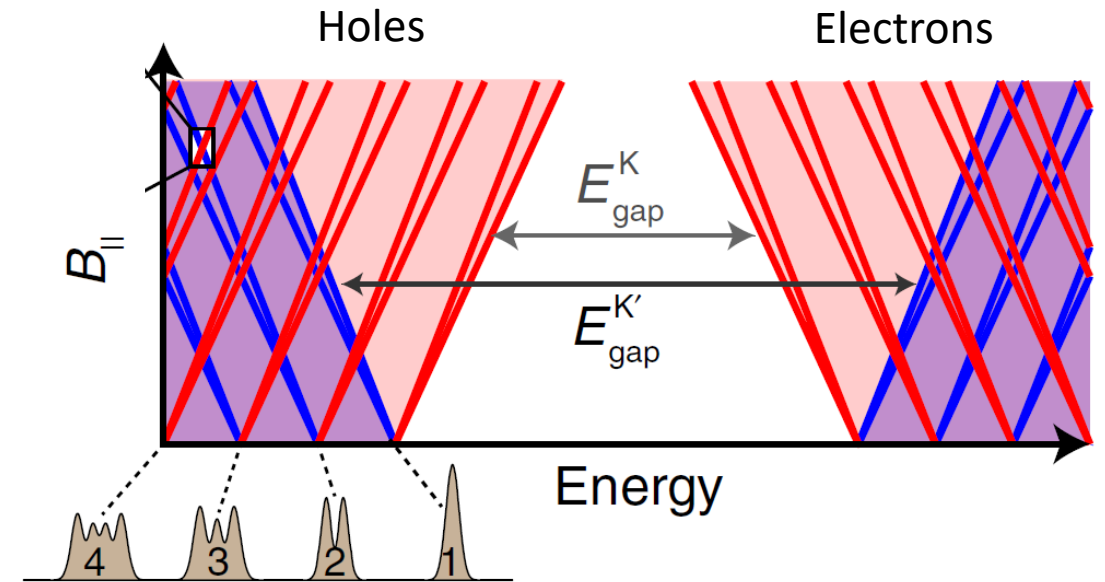
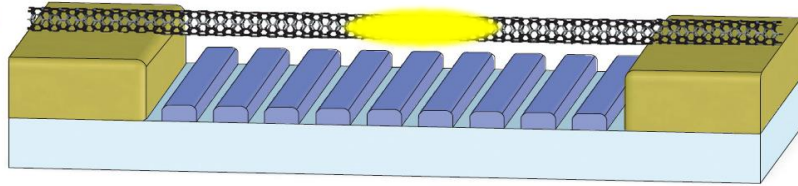
# Scanning SET



Yoo et al., *Science* 276, 579 (1997)

Lina et al., *J. Semicond.* 37, 044008 (2016)

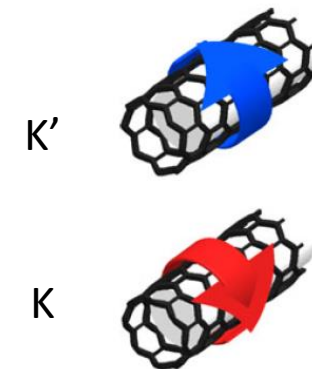
# Qubit states



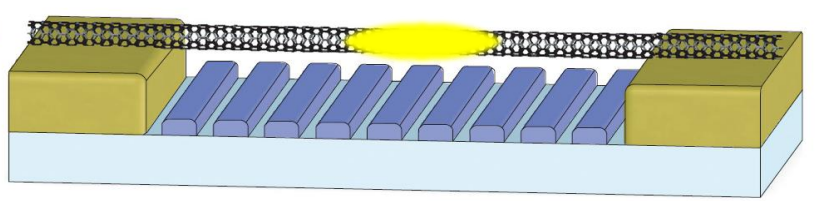
- $B //$  to CNT axis

Electronic harmonic oscillator levels in CNT:

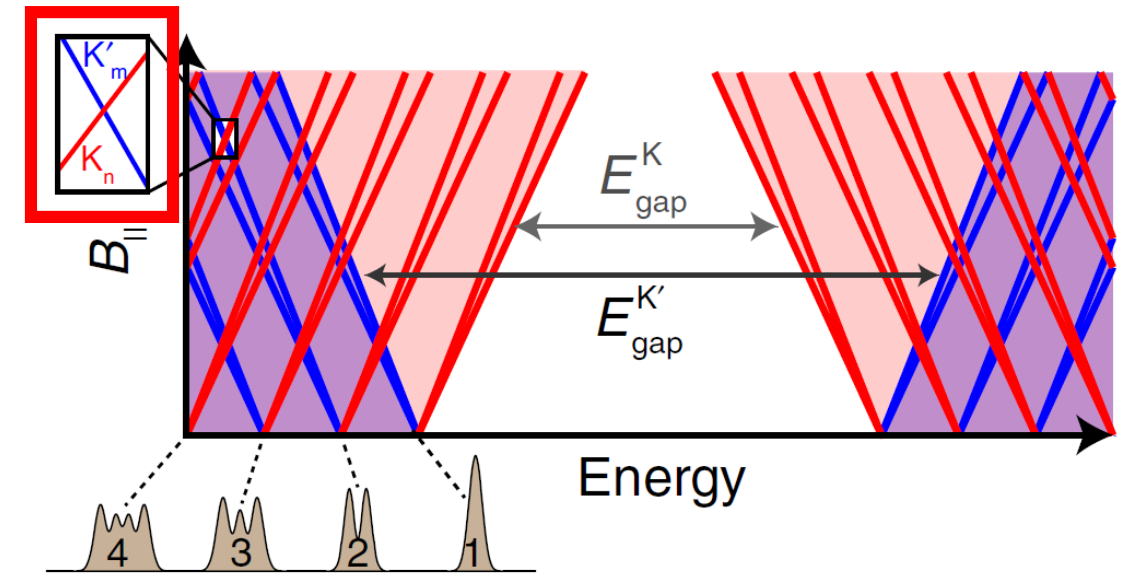
- 4-fold degenerate:
  - Spin (up, down)
  - Valley (K, K')
- Increase in level number leads to more extended wave functions



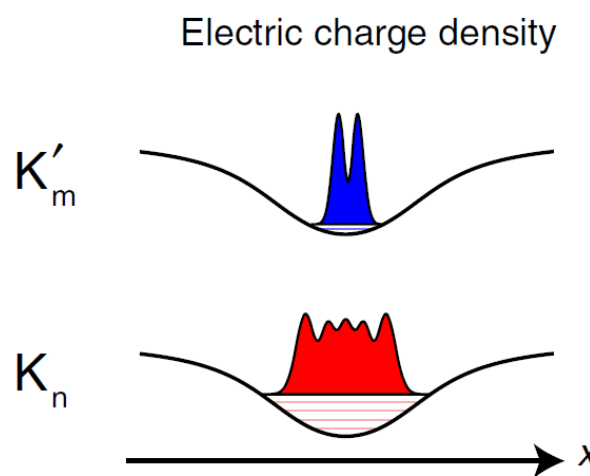
# Qubit states



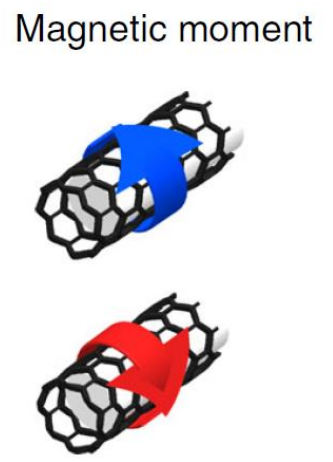
- Choose high K and low K'



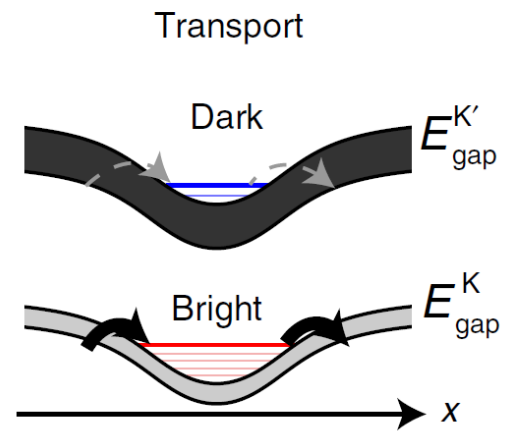
- B // to CNT axis



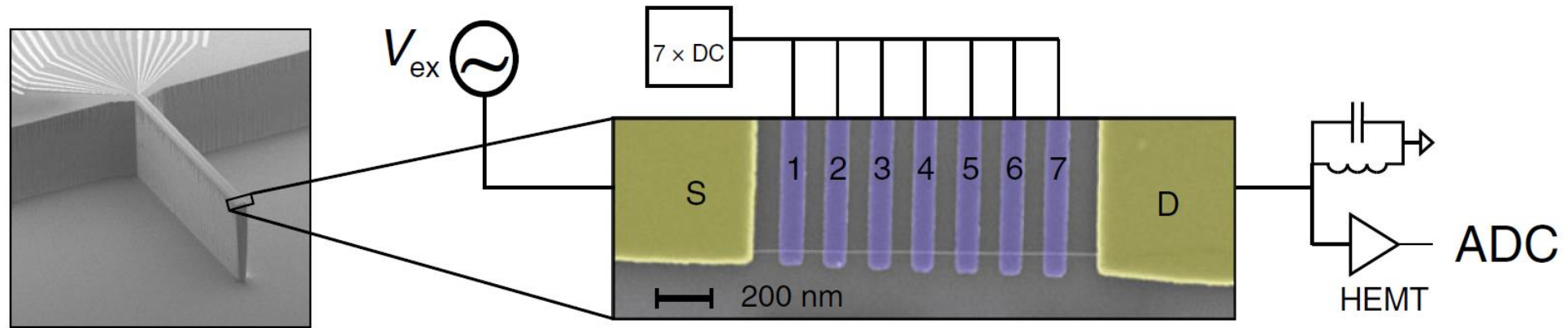
- Electric moment



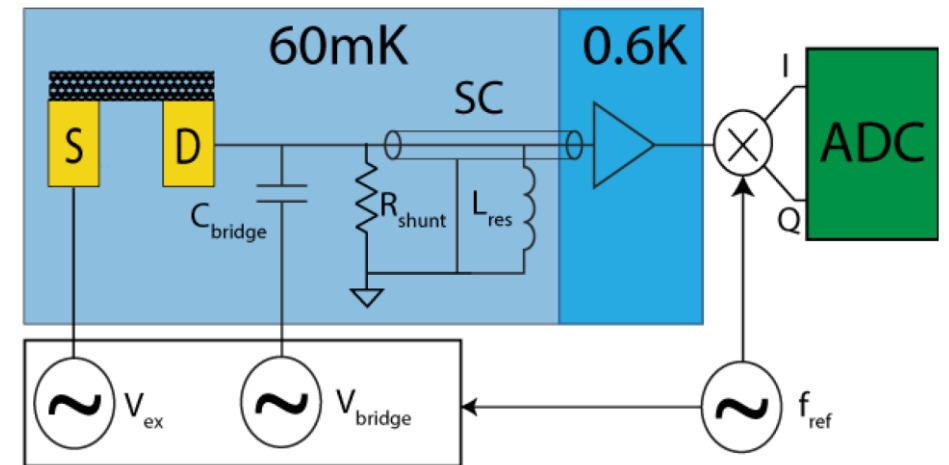
- Opposite spins, to minimize decay



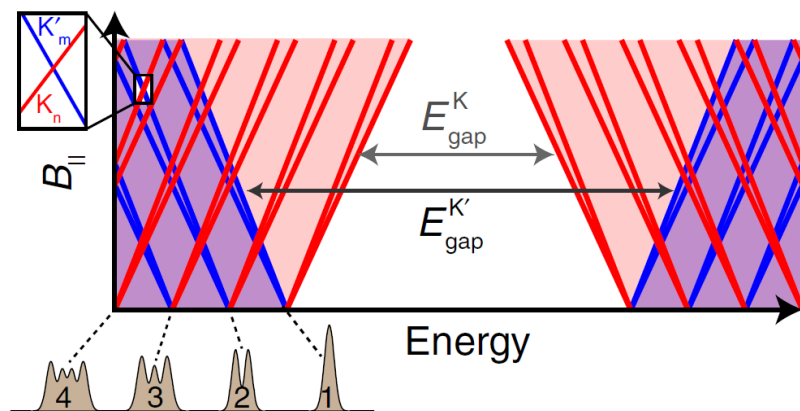
# Measurement details



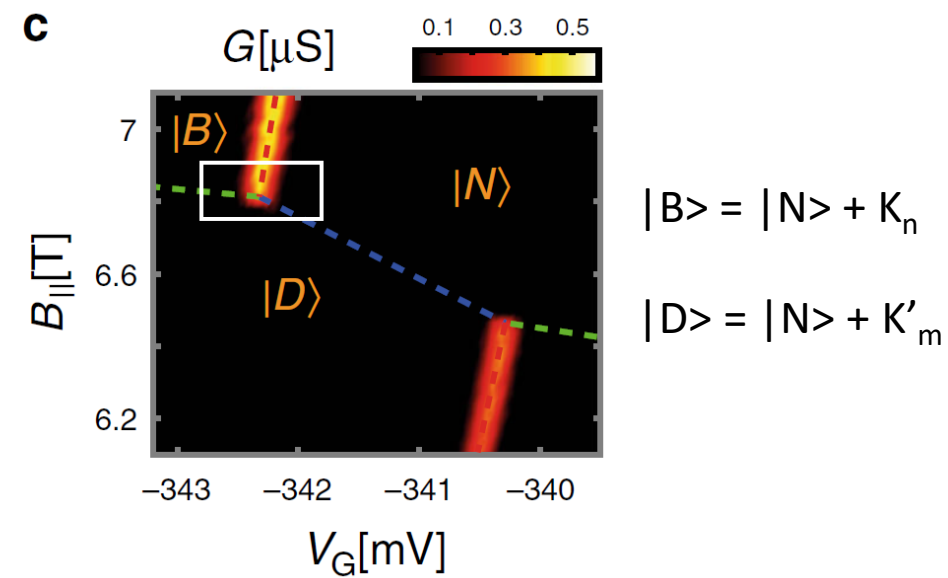
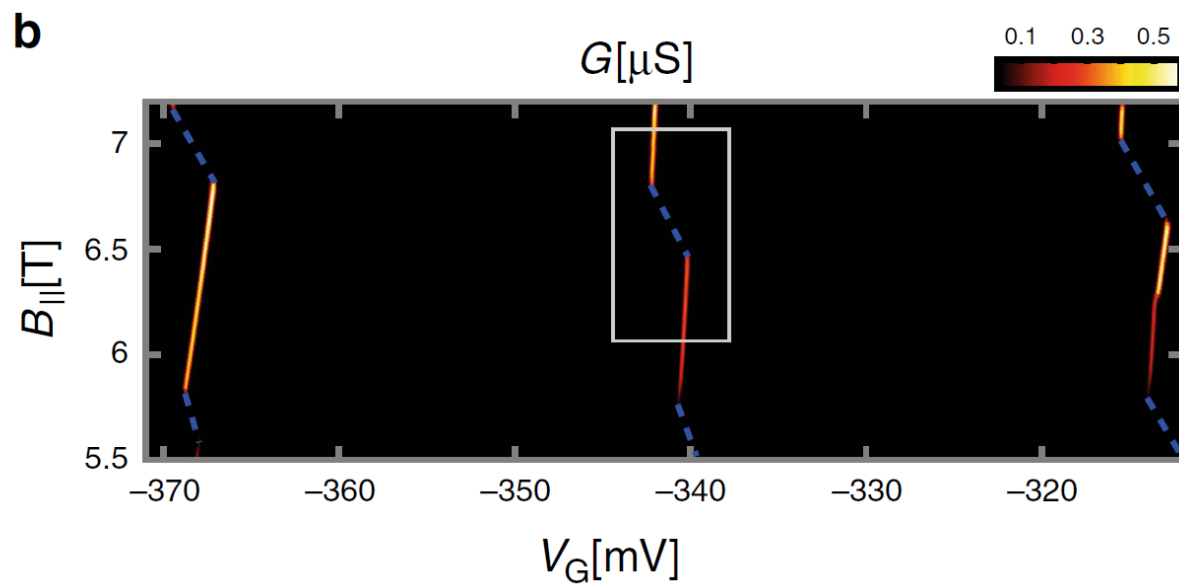
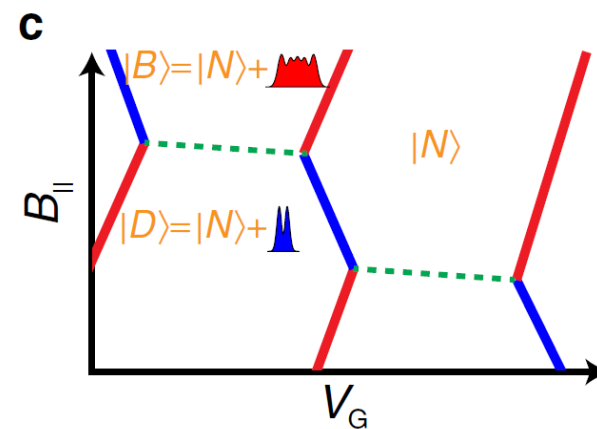
- Electron temperature: 60 mK
- Lock-in measurement using LC-circuit:
  - $f = 1.45$  MHz
  - $V_{ac} = 15 \mu V_{rms}$



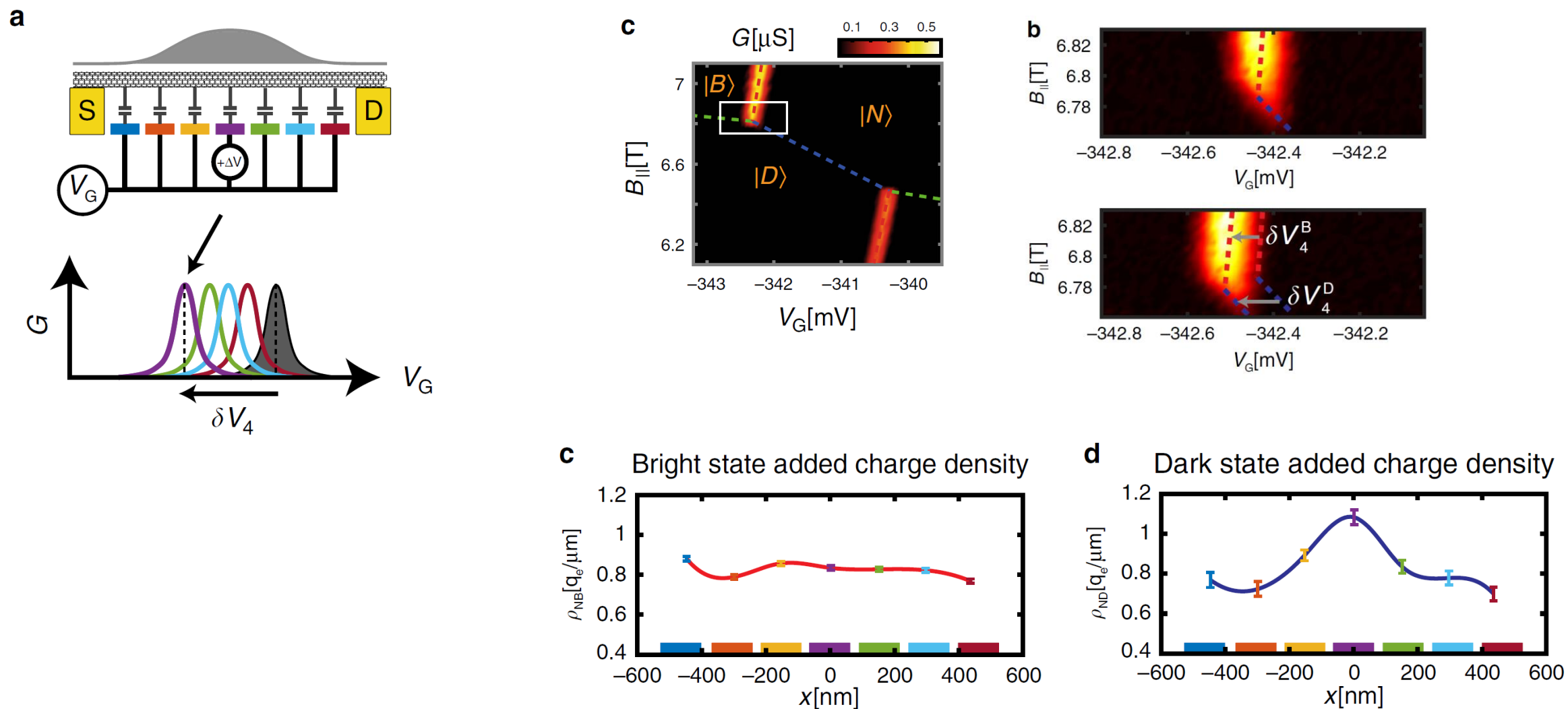
# Charge stability diagram



+ Charging energy =

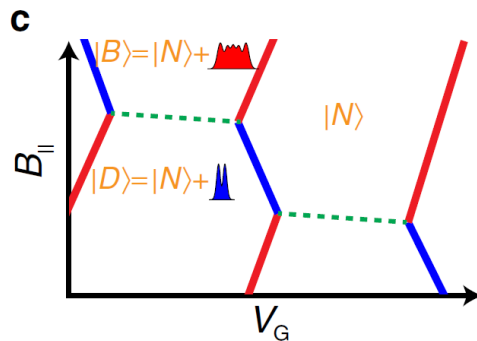
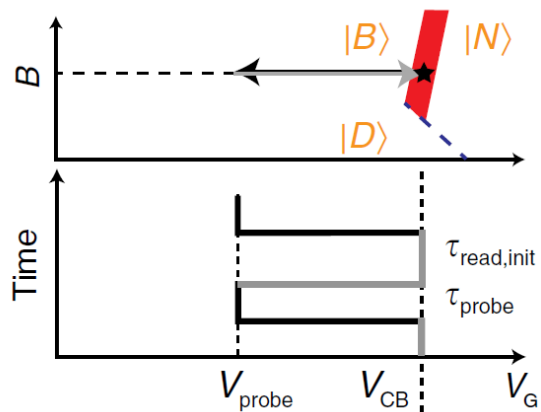


# Spatial charge distributions of the two qubit states



• Resolution:  $\sim 100$  nm

# Pulsed measurements: detection of qubit transition

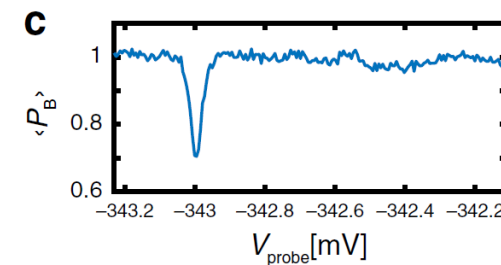
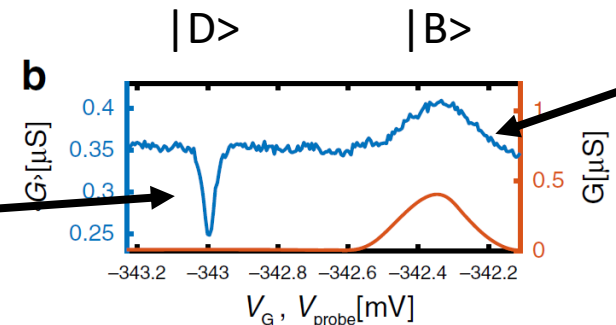


- 1) Initialize in  $|B\rangle$
- 2) Pulse to  $|B\rangle - |D\rangle$  transition
- 3) Read-out
- 4) Repeat

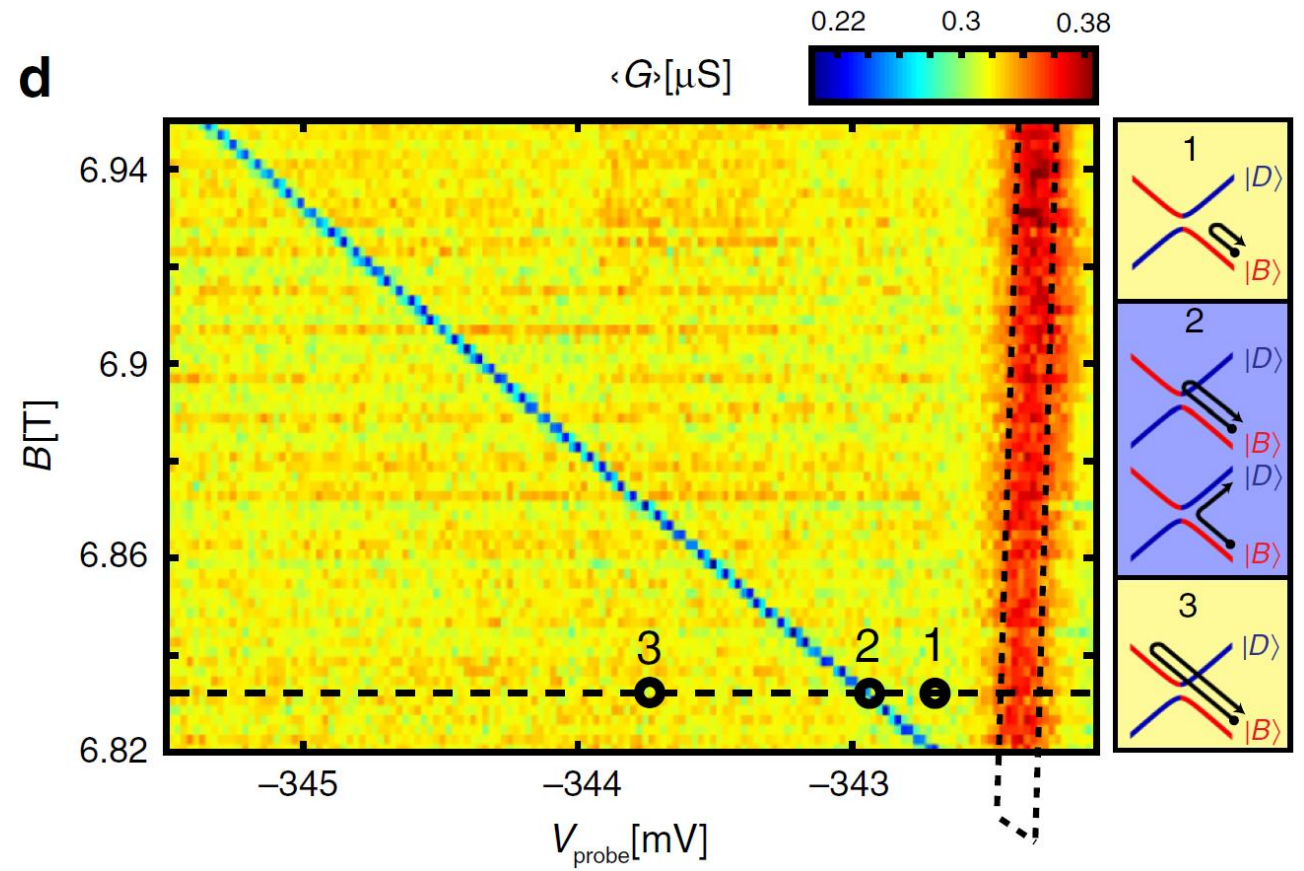
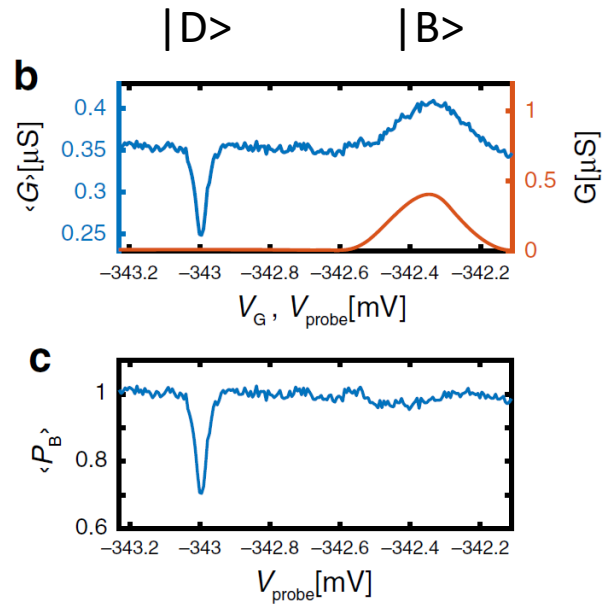
$$\langle G \rangle = \left( G(V_{\text{probe}}) \tau_{\text{probe}} + G(V_{\text{CB}}) \langle P_B \rangle \tau_{\text{read,init}} \right) / \left( \tau_{\text{probe}} + \tau_{\text{read,init}} \right)$$

- $\tau_{\text{probe}} = 0.8 \mu\text{s}$
- $\tau_{\text{read,init}} = 5 \mu\text{s}$

Qubit transition:  
40  $\mu\text{V}$



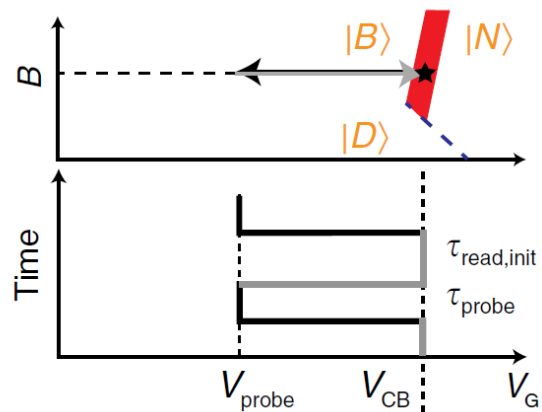
# Pulsed measurements: detection of qubit transition



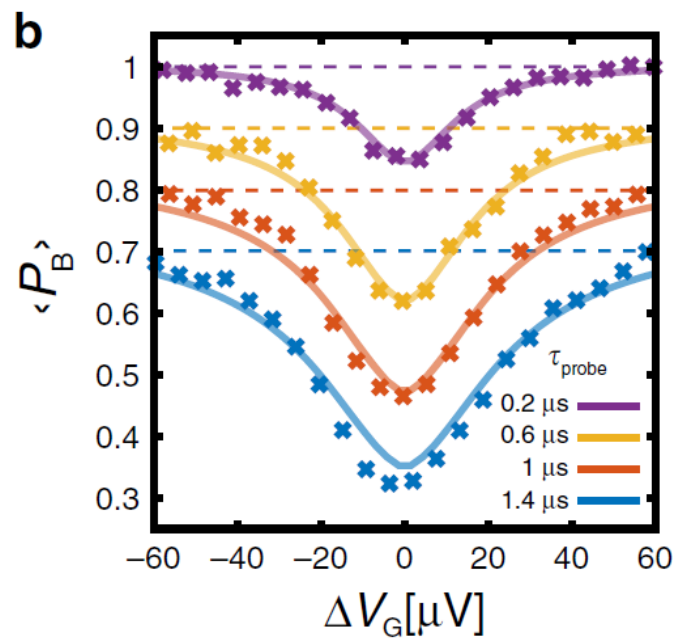
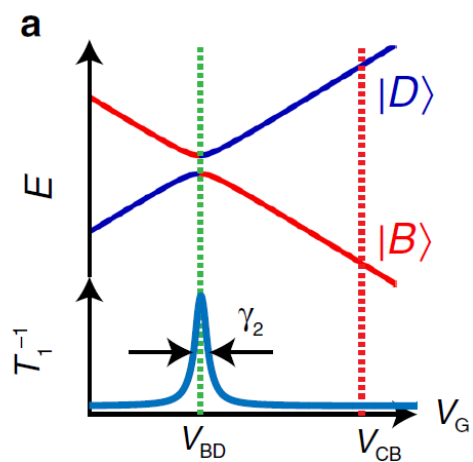
- slope: sensitive to voltages and magnetic fields



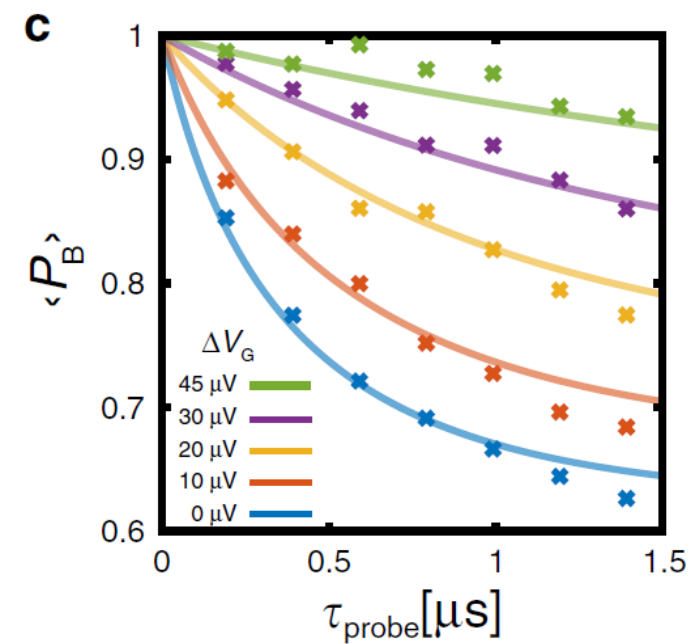
# Transition rate



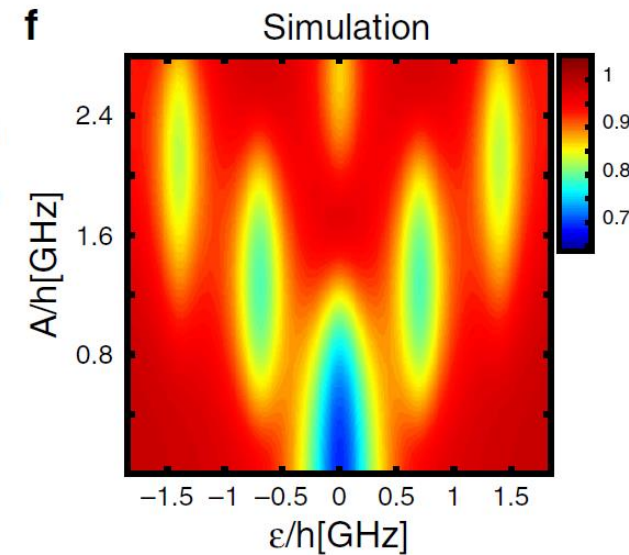
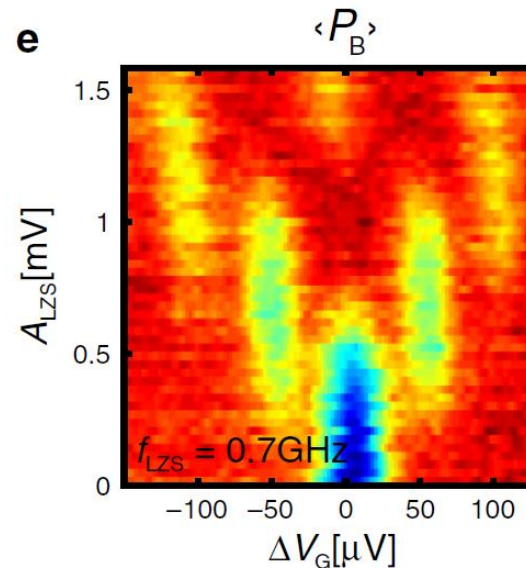
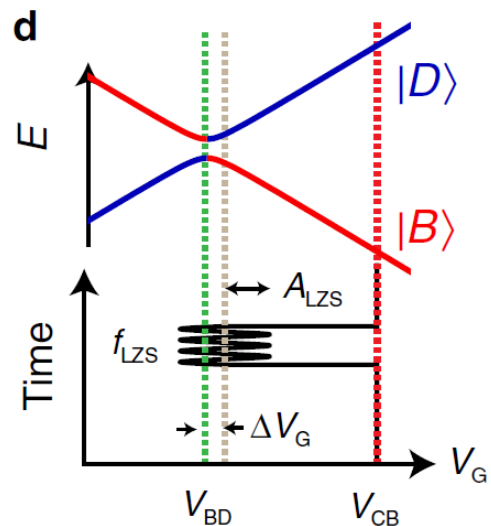
- Vary  $\tau_{\text{probe}}$
- $\tau_{\text{read,init}} = 5 \mu\text{s}$



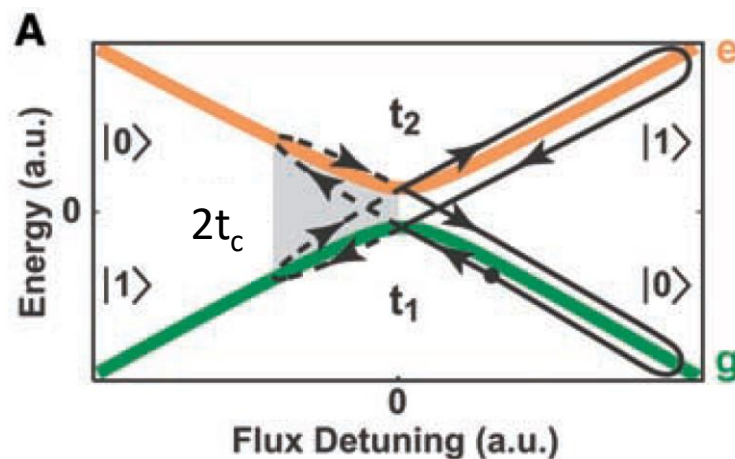
$T_1 = 1 \mu\text{s}$



# Landau-Zener-Stückelberg interferometry



$$V_G(t) = V_{BD} + \Delta V_G + A_{LZS} \sin(2\pi f_{LZS} t)$$



$$P_{LZ} = \exp\left(-2\pi \frac{(2t_c)^2}{\hbar v}\right)$$

$$v = dE/dt$$

Width:  $T_2^* = 0.9\text{ns}$  (charge noise)

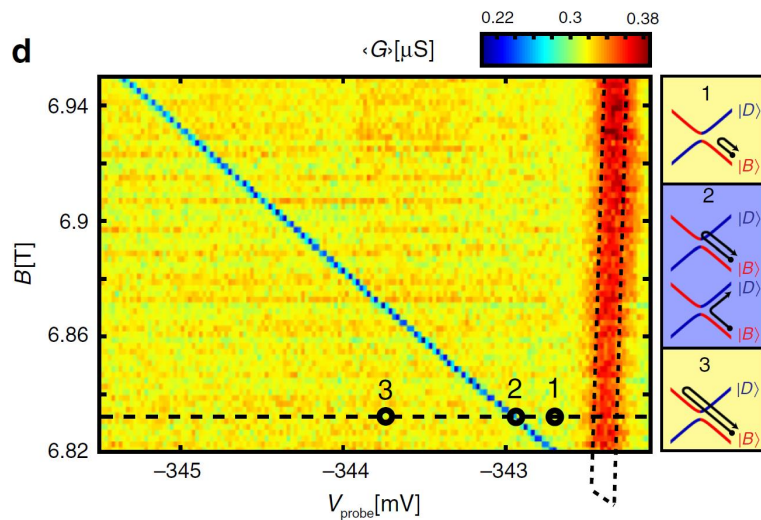
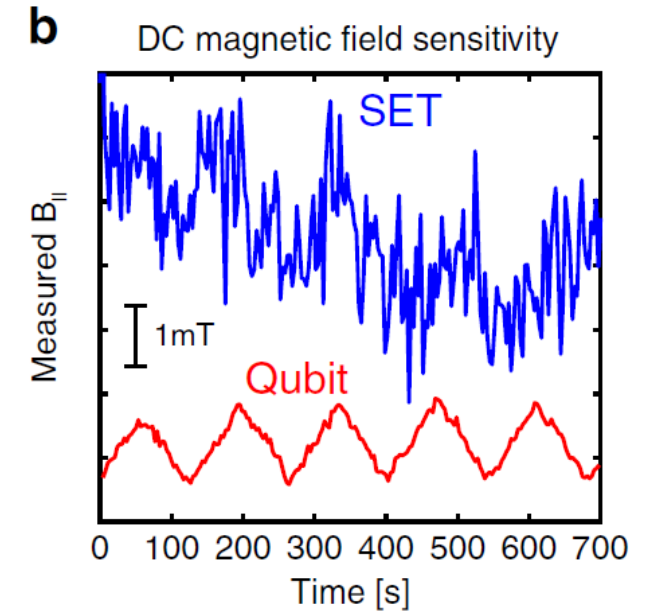
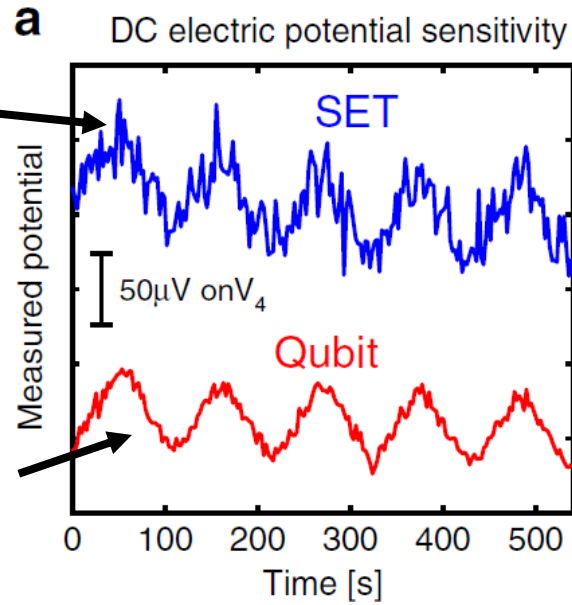
**Compare:**

- $T_2^* = 13\text{ ns}$  (on-chip spin-valley qubit)
- $T_2^* \sim 1\text{ }\mu\text{s}$  (spin qubit coupled to cavity)

# Sensitivities

On Coulomb peak

On qubit transition



- 60  $\text{neV}/\text{Hz}^{1/2}$
- 600  $\text{nV}/\text{Hz}^{1/2}$

- 39  $\mu\text{T}/\text{Hz}^{1/2}$

**Compare:**

CNT SET sensitivity: 2  $\mu\text{V}/\text{Hz}^{1/2}$

Scanning NV ac field sensitivity: 100  $\text{nT}/\text{Hz}^{1/2}$   
(stationary NV: 4  $\text{nT}/\text{Hz}^{1/2}$  (DC), 1.3  $\text{nT}/\text{Hz}^{1/2}$  (AC))

Scanning SQUID sensitivity: 5  $\text{nT}/\text{Hz}^{1/2}$

*Ella, Ilani et al., Nat. Nanotechnol. 14, 480 (2019)*

*Marchiori et al., arXiv: 2103.10382*

# *Outlook*

- Use as scanning probe
- Improve sensitivities (high contact resistance, magnet fluctuations)
- Higher than dilution temperatures
- Increase resolution (100 nm here)

*Thank you!*

## Charge distributions

$$\delta E_i^\beta = \int dx \rho_\beta(x) \phi_i(x)$$

$\phi_i(x)$ , can be calculated using electrostatic simulations

global voltage shift  $\delta V_i^{\beta_1, \beta_2}$

$$\delta V_i^{\beta_1, \beta_2} \sum_j v_j (\delta E_j^{\beta_1} - \delta E_j^{\beta_2}) = \Delta V (\delta E_i^{\beta_1} - \delta E_i^{\beta_2})$$

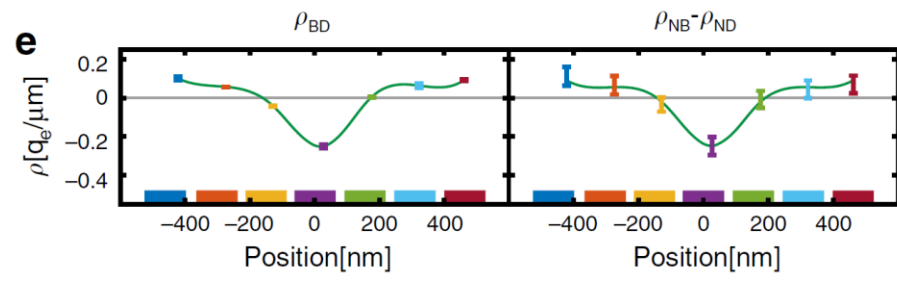
$$\rho_{\beta_1}(x_i) - \rho_{\beta_2}(x_i) = \frac{\delta V_i^{\beta_1, \beta_2}}{\Delta V} N$$

## *Relaxation and decoherence*

$$H = \frac{\epsilon(t)}{2} \sigma_z + \frac{\Delta}{2} \sigma_x$$

$$T_1^{-1}(\epsilon) = \gamma_1 + \frac{\Delta^2}{\gamma_2 + \frac{\epsilon^2}{\gamma_2}}$$

The dominant decoherence mechanism results from noise in  $\epsilon$  leading to decay of the Bloch vector to the Z axis with rate  $\gamma_2$ . In addition, a less significant noise in  $\Delta$  leads to decay to the XY plane with rate  $\gamma_1$ .





# Gate-dot capacitances

